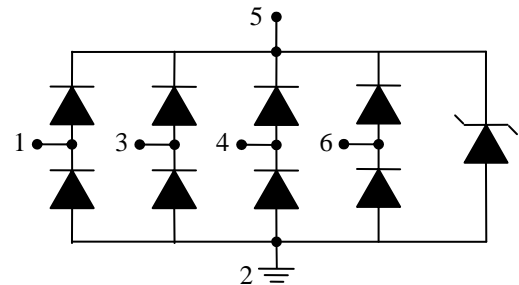
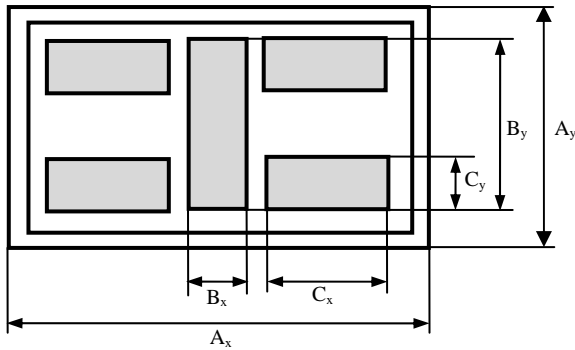


## KSR-5.0V4M1

Low capacitance TVS Diode Array



**Schematic and pinning diagram.**

**Mechanical date:**  $A_x=600\ \mu\text{m}$ ,  $A_y=420\ \mu\text{m}$ ,  
 $B_x=168\ \mu\text{m}$ ,  $B_y=472\ \mu\text{m}$   
 $C_x=356\ \mu\text{m}$ ,  $C_y=155\ \mu\text{m}$

**Chip thickness:** 138 $\pm$ 12 $\mu\text{m}$ .

**Scribe Line width** - 60 $\mu\text{m}$ .

**Top Metal:** Al - for wire bonding.

**Back side - Anode:** Ti-Ni-Ag for soldering.

### Limiting values

Parameter	Symbol	Conditions	Value	Unit
Reverse Stand-off voltage	$V_{RWM}$	-	5	V
Peak Pulse Power	$P_{pp}$	$t_p=8/20\ \mu\text{s}$	150*	W
Peak Pulse Current	$I_{pp}$	$t_p=8/20\ \mu\text{s}$	5*	A
Electrostatic Discharge	$V_{ESD}$	IEC 61000-4-2, level 4.	>12 (Contact); >17 (Air).	kV
Max.junction temperature	$T_j$	-	+150	$^{\circ}\text{C}$

### Characteristics ( $T_j=25^{\circ}\text{C}$ )

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_{BR}$	Breakdown voltage	$I_R=1\ \text{mA}$	6,1	7,0	8,5	V
$I_R$	Reverse leakage current	$V=5\ \text{V}$	-	-	0,9	$\mu\text{A}$
$V_F$	Forward voltage	$I_F=15\ \text{mA}$	-	-	1,15	V
$V_{CL}$	Clamping Voltage	$I_{pp}=1.0\ \text{A}$ , $t_p=8/20\ \mu\text{s}$	-	-	15*	V
$C_J$	Capacitance. Any I/O pin to Ground	$V_R=0\ \text{V}$ , $f=1\ \text{MHz}$	-	-	0,8	pF

\*- For Device testing